

Brian Corbett

List of Publications by Year in descending order

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340
papers

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126907

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53
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340
all docs

340
docs citations

340
times ranked

3998
citing authors

#	ARTICLE	IF	CITATIONS
1	Gain-switched dual frequency comb at 2 μm . Optics Express, 2022, 30, 5213.	3.4	5
2	Transfer Printing of Roughened GaN-Based Light-Emitting Diodes into Reflective Trenches for Visible Light Communication. Advanced Photonics Research, 2022, 3, .	3.6	6
3	Lossless High-speed Silicon Photonic MZI switch with a Micro-Transfer-Printed III-V amplifier. , 2022, , .		0
4	Integration of high performance GaN LEDs for communication systems and smart society. , 2022, , .		0
5	S-MRUT: Sectored-Multiring Ultrasonic Transducer for Selective Powering of Brain Implants. IEEE Transactions on Ultrasonics, Ferroelectrics, and Frequency Control, 2021, 68, 191-200.	3.0	9
6	Importance of Overcoming MOVPE Surface Evolution Instabilities for $>1.3 \mu\text{m}$ Metamorphic Lasers on GaAs. Crystal Growth and Design, 2021, 21, 2068-2075.	3.0	2
7	Micro-Light Emitting Diode: From Chips to Applications. Laser and Photonics Reviews, 2021, 15, 2000133.	8.7	108
8	Laser to laser power conversion with remote signaling. Optics Express, 2021, 29, 16611.	3.4	2
9	Low Noise Heterogeneous III-V-on-Silicon Mode-Locked Comb Laser. Laser and Photonics Reviews, 2021, 15, 2000485.	8.7	38
10	Wide Area Uniform Illumination Scheme Using LED Matrix for Optogenetic Cardiac Pacing. Photonics, 2021, 8, 499.	2.0	2
11	Edge-Coupling of O-Band InP Etched-Facet Lasers to Polymer Waveguides on SOI by Micro-Transfer-Printing. IEEE Journal of Quantum Electronics, 2020, 56, 1-8.	1.9	8
12	Microtransfer Printing High-Efficiency GaAs Photovoltaic Cells onto Silicon for Wireless Power Applications. Advanced Materials Technologies, 2020, 5, 2000048.	5.8	6
13	Direct visualization of phase-matched efficient second harmonic and broadband sum frequency generation in hybrid plasmonic nanostructures. Light: Science and Applications, 2020, 9, 180.	16.6	24
14	Ultrasonically Powered Compact Implantable Dust for Optogenetics. IEEE Transactions on Biomedical Circuits and Systems, 2020, 14, 583-594.	4.0	16
15	Micro-Transfer-Printed III-V-on-Silicon C-Band Semiconductor Optical Amplifiers. Laser and Photonics Reviews, 2020, 14, 1900364.	8.7	50
16	Polarization fields in semipolar ($2 \times 10^{20} \text{ cm}^{-3}$) and ($2 \times 10^{19} \text{ cm}^{-3}$) InGaN light emitting diodes. Applied Physics Letters, 2020, 116, 062106.	3.3	0
17	Transfer-print integration of GaAs p-i-n photodiodes onto silicon nitride waveguides for near-infrared applications. Optics Express, 2020, 28, 21275.	3.4	23
18	Micro-transfer-printed III-V-on-silicon C-band distributed feedback lasers. Optics Express, 2020, 28, 32793.	3.4	33

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19	Surface emitting 1.5µm multi-quantum well LED on epitaxial lateral overgrowth InP/Si. Optical Materials Express, 2020, 10, 1714.	3.0	7
20	Heterogeneous III-V on silicon nitride amplifiers and lasers via microtransfer printing. Optica, 2020, 7, 386.	9.3	84
21	Micro-transfer-printed III-V-on-silicon distributed feedback lasers. , 2020, , .		0
22	Heterogeneous integration of III-V based photonics with silicon. , 2020, , .		2
23	Realization of high efficiency ultrasound-powered micro-LEDs for optogenetics. , 2020, , .		1
24	Transfer-print integration of GaAs p-i-n photodiodes onto silicon nitride photonic integrated circuits. , 2020, , .		0
25	InAlN-based LEDs emitting in the near-UV region. Japanese Journal of Applied Physics, 2019, 58, SCCB33.	1.5	13
26	High power surface emitting InGaN superluminescent light-emitting diodes. Applied Physics Letters, 2019, 115, .	3.3	17
27	CMOS-Compatible Titanium Nitride for On-Chip Plasmonic Schottky Photodetectors. ACS Omega, 2019, 4, 17223-17229.	3.5	24
28	III-V-on-Si photonic integrated circuits realized using micro-transfer-printing. APL Photonics, 2019, 4, .	5.7	108
29	Transfer printing of III-V devices for silicon photonics. , 2019, , .		0
30	Micro-transfer-printing for heterogeneous integration. , 2019, , .		0
31	Plasmonic Schottky photodetector with metal stripe embedded into semiconductor and with a CMOS-compatible titanium nitride. Scientific Reports, 2019, 9, 6048.	3.3	41
32	III-V-on-silicon widely tunable laser realized using micro-transfer-printing. , 2019, , .		2
33	Heterogeneous integration in silicon photonics through micro-transfer-printing. , 2019, , .		0
34	Micro-transfer-printing of InP Photonic Devices to Silicon Photonics. , 2019, , .		1
35	Comparison between Different Optical Systems for Optogenetics based Head Mounted Device for Retina Pigmentosa. , 2019, 2019, 382-385.		0
36	Design guidelines for edge-coupled waveguide unitravelling carrier photodiodes with improved bandwidth. IET Optoelectronics, 2019, 13, 267-272.	3.3	2

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37	Micro-Transfer-Printed III-V-on-Silicon C-Band Distributed Bragg Reflector Laser. , 2019, , .		0
38	Multimode dynamics and modeling of free-running and optically injected Fabry-Pérot quantum-dot lasers. Physical Review A, 2019, 100, .	2.5	4
39	Micro-Transfer-Printed III-V-on-Silicon C-Band SOAs with 17 dB Gain. , 2019, , .		1
40	High power horizontal cavity surface-emitting InGaN superluminescent diode. , 2019, , .		0
41	Nanoimprint Lithography-Based Fabrication of Plasmonic Array of Elliptical Nanoholes for Dual-Wavelength, Dual-Polarisation Refractive Index Sensing. Plasmonics, 2019, 14, 951-959.	3.4	9
42	Low-power-consumption optical interconnect on silicon by transfer-printing for used in opto-isolators. Journal Physics D: Applied Physics, 2019, 52, 064001.	2.8	5
43	4×25 Gbps Polarization Diversity Silicon Photonics Receiver With Transfer Printed III-V Photodiodes. IEEE Photonics Technology Letters, 2019, 31, 287-290.	2.5	10
44	High-yield parallel transfer print integration of III-V substrate-illuminated C-band photodiodes on silicon photonic integrated circuits. , 2019, , .		4
45	Transfer-printing for heterogeneous integration. , 2019, , .		2
46	III-V/Si PICs based on micro-transfer-printing. , 2019, , .		6
47	Time to Open the 2- $\frac{1}{4}$ m Window?. Optics and Photonics News, 2019, 30, 42.	0.5	37
48	Integrated demultiplexing and amplification of coherent optical combs. Optics Express, 2019, 27, 16012.	3.4	2
49	Automated heterodyne method to characterize semiconductor based akinetic swept laser sources. , 2019, , .		0
50	Three-Dimensional Self-Assembled Columnar Arrays of AlInP Quantum Wires for Polarized Micrometer-Sized Amber Light Emitting Diodes. ACS Photonics, 2018, 5, 1318-1325.	6.6	4
51	Size-Dependent Bandwidth of Semipolar ($\overline{\{2\}2}$) Light-Emitting-Diodes. IEEE Photonics Technology Letters, 2018, 30, 439-442.	2.5	32
52	4Å–25Gbit/s Silicon Photonics Tunable Receiver using Transfer Printed III-V Photodiodes. , 2018, , .		0
53	Low loss photonic nanocavity via dark magnetic dipole resonant mode near metal. Scientific Reports, 2018, 8, 17054.	3.3	1
54	Thermal Analysis of InP Lasers Transfer Printed to Silicon Photonics Substrates. Journal of Lightwave Technology, 2018, 36, 5935-5941.	4.6	17

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55	Characterization of a Low-Cost, Monolithically Integrated, Tunable 10G Transmitter for Wavelength Agile PONs. IEEE Journal of Quantum Electronics, 2018, 54, 1-12.	1.9	2
56	Transfer Printing for Silicon Photonics. Semiconductors and Semimetals, 2018, 99, 43-70.	0.7	23
57	Transfer-printing-based integration of a III-V-on-silicon distributed feedback laser. Optics Express, 2018, 26, 8821.	3.4	98
58	Key enabling technologies for optical communications at 2000nm. Applied Optics, 2018, 57, E64.	1.8	31
59	Transfer Printing for Silicon Photonics Transceivers and Interposers. , 2018, , .		3
60	Substrate InP-based 1.5 μm lasers using an internal carbon-doped layer to block dopant diffusion. Microwave and Optical Technology Letters, 2018, 60, 2363-2367.	1.4	1
61	On-chip optical interconnect on silicon by transfer printing. , 2018, , .		2
62	Transfer print techniques for heterogeneous integration of photonic components. Progress in Quantum Electronics, 2017, 52, 1-17.	7.0	141
63	Enabling photonic technologies at 2 μm. , 2017, , .		0
64	50Gb/s InP-base Mach-Zehnder modulator. , 2017, , .		0
65	Study of high order plasmonic modes on ceramic nanodisks. Optics Express, 2017, 25, 5244.	3.4	8
66	Silicon photonics fiber-to-the-home transceiver array based on transfer-printing-based integration of III-V photodetectors. Optics Express, 2017, 25, 14290.	3.4	44
67	Air-clad broadband waveguide using micro-molded polyimide combined with a robust, silica-based inverted opal substrate. Optical Materials Express, 2017, 7, 3155.	3.0	4
68	Comparison of InGaAs and InAlAs sacrificial layers for release of InP-based devices. Optical Materials Express, 2017, 7, 4408.	3.0	28
69	Surface Micromachined MEMS-Tunable PIN-Photodiodes around 1550-nm. , 2017, , .		2
70	Transferred III-V Materials - Novel Devices and Integration. , 2017, , .		0
71	A 10Gbps optical burst switching network incorporating ultra-fast (5ns) wavelength switched tunable laser sources. , 2017, , .		0
72	Lithographically Defined, Room Temperature Low Threshold Subwavelength Red-Emitting Hybrid Plasmonic Lasers. Nano Letters, 2016, 16, 7822-7828.	9.1	23

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73	Wheatstone bridge configuration for evaluation of plasmonic energy transfer. Scientific Reports, 2016, 6, 24423.	3.3	1
74	Combined electrical and resonant optical excitation characterization of multi-quantum well InGaN-based light-emitting diodes. AIP Advances, 2016, 6, 075108.	1.3	4
75	Exciton localization in semipolar (112 $\hat{\text{A}}^2$) InGaN multiple quantum wells. Journal of Applied Physics, 2016, 120, 055705.	2.5	2
76	Transfer Printing of AlGaInAs/InP Etched Facet Lasers to Si Substrates. IEEE Photonics Journal, 2016, 8, 1-10.	2.0	36
77	Role of substrate quality on the performance of semipolar (112 $\hat{\text{A}}^2$) InGaN light-emitting diodes. Journal of Applied Physics, 2016, 120, .	2.5	8
78	Low-linewidth and tunable single frequency 1x2 multimode-interferometer-Fabry-Perot laser diode. Proceedings of SPIE, 2016, , .	0.8	0
79	Study of TiN nanodisks with regard to application for Heat-Assisted Magnetic Recording. MRS Advances, 2016, 1, 317-326.	0.9	13
80	Comparative study of (0001) and (11 $\hat{\text{A}}^2$) InGaN based light emitting diodes. Japanese Journal of Applied Physics, 2016, 55, 05FJ10.	1.5	7
81	AlGaAs ridge laser with 33% wall-plug efficiency at 100 $\hat{\text{A}}^{\circ}\text{C}$ based on a design of experiments approach. Semiconductor Science and Technology, 2016, 31, 045002.	2.0	2
82	Fluorescence microscopy investigation of InGaN-based light-emitting diodes. IET Optoelectronics, 2016, 10, 39-43.	3.3	1
83	High Bandwidth Freestanding Semipolar (11 $\hat{\text{A}}^2$) InGaN/GaN Light-Emitting Diodes. IEEE Photonics Journal, 2016, 8, 1-8.	2.0	18
84	Monolithically integrated low linewidth comb source using gain switched slotted Fabry-Perot lasers. Optics Express, 2016, 24, 7960.	3.4	24
85	Bloch surface wave structures for high sensitivity detection and compact waveguiding. Science and Technology of Advanced Materials, 2016, 17, 398-409.	6.1	36
86	Three-coherent-output narrow-linewidth and tunable single frequency 1x2 multi-mode-interferometer laser diode. Optics Express, 2016, 24, 5846.	3.4	6
87	Integrated plasmonic circuitry on a vertical-cavity surface-emitting semiconductor laser platform. Nature Communications, 2016, 7, 12409.	12.8	24
88	Exploring a new transmission window for telecommunications in the 2 $\hat{\text{A}}^{\mu}\text{m}$ waveband. , 2016, , .		1
89	Monolithically integrated low-cost 10Gb/s tuneable transmitter using a slotted Fabry-Perot laser. , 2016, , .		0
90	Enabling technologies for a new wavelength window at 2microns. , 2016, , .		0

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91	Study of electro-optic effect in asymmetrically ramped AlInGaAs multiple quantum well structures. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 930-935.	1.8	2
92	Thermal modelling of transfer-bonded thin-film gallium arsenide laser diode. IET Optoelectronics, 2016, 10, 51-56.	3.3	4
93	Scalable electro-photonics integration concept based on polymer waveguides. Proceedings of SPIE, 2016, , .	0.8	1
94	Development of semipolar (11-22) LEDs on GaN templates. Proceedings of SPIE, 2016, , .	0.8	8
95	Novel Mach-Zehnder Interferometer Waveguide Design as a Light Delivery System for Heat-Assisted Magnetic Recording. IEEE Transactions on Magnetics, 2016, 52, 1-7.	2.1	3
96	40 Gb/s WDM Transmission Over 1.15-km HC-PBGF Using an InP-Based Mach-Zehnder Modulator at 2 μ m. Journal of Lightwave Technology, 2016, 34, 1706-1711.	4.6	30
97	Exciton localization in polar and semipolar (112̄...2) In _{0.2} Ga _{0.8} N/GaN multiple quantum wells. Semiconductor Science and Technology, 2016, 31, 085006.	2.0	7
98	Impact of DWDM at 50GHz spacing in the 2 μ m waveband. , 2016, , .		2
99	GHz bandwidth semipolar (112̄ ²) InGaN/GaN light-emitting diodes. Optics Letters, 2016, 41, 5752.	3.3	40
100	Wavelength-stabilised Low-cost 10 Gb/s Tuneable Slotted Fabry-Pérot Laser. , 2016, , .		0
101	High Bandwidth (11-22) Semipolar LEDs for Visible Light Communications. , 2016, , .		0
102	Quantum Well Intermixing in 2 μ m InGaAs Multiple Quantum Well structures. , 2016, , .		0
103	AlInGaAs surface normal photodiode for 2 μ m optical communication systems. , 2015, , .		8
104	40 Gbps WDM transmission over 1.15 km HC-PBGF using the first InP-based Mach Zehnder modulator at 2 μ m. , 2015, , .		0
105	Novel droplet near-field transducer for heat-assisted magnetic recording. Nanophotonics, 2015, 4, 503-510.	6.0	20
106	Semipolar (202̄...3) nitrides grown on 3C-SiC/(001) Si substrates. Semiconductor Science and Technology, 2015, 30, 125007.	2.0	10
107	Semipolar (112) InGaN light-emitting diodes grown on chemically-mechanically polished GaN templates. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 2196-2200.	1.8	17
108	Adhesive bonding for mechanically stacked solar cells. Progress in Photovoltaics: Research and Applications, 2015, 23, 1080-1090.	8.1	28

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109	Transfer printing of fully formed thin-film microscale GaAs lasers on silicon with a thermally conductive interface material. <i>Laser and Photonics Reviews</i> , 2015, 9, L17.	8.7	36
110	Semiconductor Quantum Well Lasers With a Temperature-Insensitive Threshold Current. <i>IEEE Journal of Selected Topics in Quantum Electronics</i> , 2015, 21, 177-182.	2.9	4
111	Numerical simulations with energy balance model for unitraveling-carrier photodiode. , 2015, , .		0
112	Trap enhanced Ge/Si photodiode formed by direct bonding: Towards NIR imaging system. , 2015, , .		0
113	Over 20MHz modulation bandwidth on 250nm emission of AlGaIn micro-LEDs. <i>Electronics Letters</i> , 2015, 51, 354-355.	1.0	5
114	InGaAs Surface Normal Photodiode for 2 μm \times μm Optical Communication Systems. <i>IEEE Photonics Technology Letters</i> , 2015, 27, 1469-1472.	2.5	15
115	Color stability, wave function overlap and leakage currents in InGaIn-based LED structures: the role of the substrate orientation. <i>Semiconductor Science and Technology</i> , 2015, 30, 055014.	2.0	4
116	Enhanced performance of graphene-based electro-absorption waveguide modulators by engineered optical modes. <i>Journal Physics D: Applied Physics</i> , 2015, 48, 235101.	2.8	21
117	100 Gbit/s WDM transmission at 2 μm : transmission studies in both low-loss hollow core photonic bandgap fiber and solid core fiber. <i>Optics Express</i> , 2015, 23, 4946.	3.4	111
118	10 Gb/s InP-based Mach-Zehnder modulator for operation at 2 μm wavelengths. <i>Optics Express</i> , 2015, 23, 10905.	3.4	13
119	Multi-level single mode 2D polymer waveguide optical interconnects using nano-imprint lithography. <i>Optics Express</i> , 2015, 23, 14630.	3.4	34
120	Dense WDM transmission at 2 μm enabled by an arrayed waveguide grating. <i>Optics Letters</i> , 2015, 40, 3308.	3.4	42
121	MHz operation of 250 nm ultra-violet micro-light emitting diodes. , 2015, , .		0
122	250-nm emitting LED optimized for optical fibre coupling. , 2015, , .		1
123	InP-Based Active and Passive Components for Communication Systems at 2 μm . <i>Journal of Lightwave Technology</i> , 2015, 33, 971-975.	4.6	44
124	Design, fabrication and characterisation of nano-imprinted single mode waveguide structures for intra-chip optical communications. , 2015, , .		0
125	Optical coupling structure made by imprinting between single-mode polymer waveguide and embedded VCSEL. <i>Proceedings of SPIE</i> , 2015, , .	0.8	1
126	Towards AlN optical cladding layers for thermal management in hybrid lasers. , 2015, , .		4

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127	Low defect large area semi-polar (112) GaN grown on patterned (113) silicon. Physica Status Solidi (B): Basic Research, 2015, 252, 1104-1108.	1.5	16
128	Design and fabrication tolerance analysis of multimode interference couplers. Optics Communications, 2015, 340, 26-32.	2.1	12
129	Spectral analysis of In _x Ga _{1-x} N/GaN quantum well structures for III-nitride based solar cells. , 2014, , .		0
130	Demonstration of 90° optical hybrid at 2 μm wavelength range based on 4×4 MMI using diluted waveguide. , 2014, , .		0
131	Phase matched transmission line design for high-speed optical modulators. , 2014, , .		1
132	81 Gb/s WDM transmission at 2¼m over 1.15 km of low-loss hollow core photonic bandgap fiber. , 2014, , .		10
133	Dual resonance approach to decoupling surface and bulk attributes in photonic crystal biosensor. Optics Letters, 2014, 39, 6213.	3.3	6
134	Laser Integration with CMOS Assembly Process for Si Photonics. , 2014, , .		1
135	Semiconductor Quantum Well Lasers with a Temperature Insensitive Threshold Current. , 2014, , .		1
136	Wavelength Agile Slotted Fabry-Pérot Lasers. , 2014, , .		3
137	First demonstration of a 2¼m few-mode TDFA for mode division multiplexing. Optics Express, 2014, 22, 10544.	3.4	9
138	InP based active and passive components for communication systems at 2 μm. , 2014, , .		2
139	Efficient Modelling Approach for an InP based Mach-Zehnder modulator. , 2014, , .		0
140	Few-Mode TDFA for Mode Division Multiplexing at 2 μm. , 2014, , .		2
141	Polarization matching design of InGaN-based semi-polar quantum wells – A case study of (112) orientation. Applied Physics Letters, 2014, 104, .	3.3	8
142	Development of photonic crystal structures for on-board optical communication. Proceedings of SPIE, 2014, , .	0.8	2
143	High aspect ratio nano-fabrication of photonic crystal structures on glass wafers using chrome as hard mask. Nanotechnology, 2014, 25, 355301.	2.6	24
144	Novel InGaAlAs/InGaAlAs quantum well multimode-interferometer-Fabry-Perot laser diode. , 2014, , .		0

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145	Reconfigurable Modal Gain Control of a Few-Mode EDFA Supporting Six Spatial Modes. IEEE Photonics Technology Letters, 2014, 26, 1100-1103.	2.5	74
146	20 Å– 960-Gb/s Space-division-multiplexed 32QAM transmission over 60 km few-mode fiber. Optics Express, 2014, 22, 749.	3.4	49
147	Polymer-based optical interconnects using nanoimprint lithography. , 2013, , .		4
148	Monolithic Integration of Single Facet Slotted Laser, SOA, and MMI Coupler. IEEE Photonics Technology Letters, 2013, 25, 257-260.	2.5	8
149	InAlAs solar cell on a GaAs substrate employing a graded InxGa1-xAs InP metamorphic buffer layer. Applied Physics Letters, 2013, 102, .	3.3	23
150	PIN-photodiode with a large spot size input waveguide. Optical and Quantum Electronics, 2013, 45, 365-371.	3.3	0
151	Polarizers in an Asymmetric Twin Waveguide Based on Resonant Coupling. IEEE Photonics Technology Letters, 2013, 25, 1301-1304.	2.5	3
152	Hybrid Integration of the Wavelength-Tunable Laser With a Silicon Photonic Integrated Circuit. Journal of Lightwave Technology, 2013, 31, 3934-3942.	4.6	51
153	Three mode Er ³⁺ ring-doped fiber amplifier for mode-division multiplexed transmission. Optics Express, 2013, 21, 10383.	3.4	56
154	High-Speed Substrate-Emitting Micro-Light-Emitting Diodes for Applications Requiring High Radiance. Applied Physics Express, 2013, 6, 022102.	2.4	32
155	WDM Transmission at 2 ¹ / ₄ m over Low-Loss Hollow Core Photonic Bandgap Fiber. , 2013, , .		5
156	Ge/Si heterojunction photodiodes fabricated by low temperature wafer bonding. Optics Express, 2013, 21, 17309.	3.4	19
157	Stable locking phase limits of optically injected semiconductor lasers. Optics Express, 2013, 21, 30126.	3.4	5
158	On-chip optical phase locking of single growth monolithically integrated slotted fabry perot lasers. Optics Express, 2013, 21, 17315.	3.4	9
159	Butterfly packaged high-speed and low leakage InGaAs quantum well photodiode for 2000nm wavelength systems. Electronics Letters, 2013, 49, 281-282.	1.0	24
160	Strategies for integration of lasers on silicon. Semiconductor Science and Technology, 2013, 28, 094001.	2.0	17
161	Few-mode EDFA Supporting 5 Spatial Modes with Reconfigurable Differential Modal Gain Control. , 2013, , .		3
162	2.576Tb/s (23256Gb/s) Mode Division Multiplexed 4PAM over 11.8 km Differential Mode Delay Uncompensated Few-Mode Fiber using Direct Detection. , 2013, , .		0

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163	20 x 960-Gb/s MDM-DP-32QAM transmission over 60km FMF with inline MM-EDFA. , 2013, , .		3
164	Multimode EDFA performance in mode-division multiplexed transmission systems. , 2013, , .		4
165	Two Color Approach to Separating Surface and Bulk Sensitivity in a Photonic Crystal Biosensor. , 2013, , .		1
166	High Capacity Multi-Mode Transmission Systems Using Higher-Order Modulation Formats. , 2013, , .		0
167	10â€¦Gbit/s transmission over 50â€¦km of SMF using MEMS tunable VCSEL. Electronics Letters, 2012, 48, 394. 1.0		3
168	737 Tb/s (96 x 3 x 256-Gb/s) mode-division-multiplexed DP-16QAM transmission with inline MM-EDFA. Optics Express, 2012, 20, B428.	3.4	156
169	High index contrast optical platform using gallium phosphide on sapphire: an alternative to SOI?. Proceedings of SPIE, 2012, , .	0.8	5
170	Air-bridge high-speed InGaAs/InP waveguide photodiode. , 2012, , .		0
171	Investigation of active filter using injection-locked slotted Fabryâ€™Perot semiconductor laser. Applied Optics, 2012, 51, 7357.	1.8	14
172	Polarization tunable transmission through plasmonic arrays of elliptical nanopores. Optics Express, 2012, 20, 25325.	3.4	33
173	Characterization of germanium/silicon <i>pâ€™n</i> junction fabricated by low temperature direct wafer bonding and layer exfoliation. Applied Physics Letters, 2012, 100, .	3.3	27
174	Coherent comb generation using integrated slotted fabry-perot semiconductor lasers. , 2012, , .		1
175	SiNx-induced intermixing in AlInGaAs/InP quantum well through interdiffusion of group III atoms. Journal of Applied Physics, 2012, 112, .	2.5	5
176	Inductively coupled plasma deep etching of InP/InGaAsP in Cl2/CH4/H2 based chemistries with the electrode at 20â€™%Â°C. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2012, 30, 051208.	1.2	12
177	Compact Electroabsorption Modulators for Photonic Integrated Circuits, Using an Isolated Pedestal Contact Scheme. IEEE Photonics Technology Letters, 2012, 24, 356-358.	2.5	8
178	20Gbit/s two LP<inf>11</inf> modes transmission over 10km two-moded fiber without crosstalk compensation. , 2012, , .		0
179	Ge/Si p-n Diode Fabricated by Direct Wafer Bonding and Layer Exfoliation. ECS Transactions, 2012, 45, 131-139.	0.5	4
180	Quantum well intermixing in AlInGaAs QW structures through the interdiffusion of group III atoms. Proceedings of SPIE, 2012, , .	0.8	0

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181	Single facet slotted Fabry-Perot laser and its application in photonic integrated circuits. Proceedings of SPIE, 2012, , .	0.8	1
182	Current transport through an n-doped, nearly lattice matched GaN/AlInN/GaN heterostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 931-933.	0.8	3
183	High speed AlInGaAs/InGaAs quantum well waveguide photodiode for wavelengths around 2 microns. , 2012, , .		1
184	Slotted tunable laser with monolithic integrated mode coupler. , 2012, , .		0
185	Multiple coherent outputs from single growth monolithically integrated injection locked tunable lasers. , 2012, , .		5
186	Voltage Spectroscopy and the Operating State of an Optically Injected Long Wavelength VCSEL. IEEE Photonics Technology Letters, 2012, 24, 1245-1247.	2.5	1
187	Sub 10 ps Carrier Response Times in Electroabsorption Modulators Using Quantum Well Offsetting. IEEE Journal of Quantum Electronics, 2012, 48, 1467-1475.	1.9	4
188	Dielectric-Free Fabrication of Compact 30-GHz Photodetectors Using the Isolated Pedestal Contact Configuration. IEEE Photonics Technology Letters, 2012, 24, 1082-1084.	2.5	2
189	Growth optimization and characterization of lattice-matched Al _{0.82} In _{0.18} N optical confinement layer for edge emitting nitride laser diodes. Journal of Crystal Growth, 2012, 338, 20-29.	1.5	10
190	Wafer-scale integration of group III-V lasers on silicon using transfer printing of epitaxial layers. Nature Photonics, 2012, 6, 610-614.	31.4	218
191	Theoretical performance of multi-junction solar cells combining III-V and Si materials. Optics Express, 2012, 20, A754.	3.4	33
192	TE/TM-mode pass polarizers and splitter based on an asymmetric twin waveguide and resonant coupling. Optical and Quantum Electronics, 2012, 44, 175-181.	3.3	4
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194	73.7 Tb/s (96Å–3Å–256-Gb/s) mode-division-multiplexed DP-16QAM transmission with inline MM-EDFA. , 2012, , .		31
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